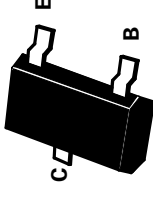


**SOT23 NPN SILICON PLANAR
SWITCHING TRANSISTOR**

ISSUE 2 – SEPTEMBER 95

**BSS79B
BSS79C**

PARTMARKING DETAILS - BSS79B - CE
BSS79C - CF



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Peak Pulse Current	I_{CM}	800	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{TOT}	330	mW
Operating and Storage Temperature Range	t_j, t_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	75		V	$I_C=10\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40		V	$I_C=10mA$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6		V	$I_E=10\mu A$
Collector Base Cut-Off Current	I_{CBO}		10 10	nA μA	$V_{CB}=60V, T_{amb}=150^{\circ}C$
Emitter Base Cut-Off Current	I_{EBO}		10	nA	$V_{BE}=3.0V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.3 1.0	V	$I_C=150mA, I_B=15mA$ $I_C=500mA, I_B=50mA$
Static Forward Current Transfer Ratio	BSS79B BSS79C	h_{FE}	40 100		$I_C=150mA, V_{CE}=10V$ $I_C=150mA, V_{CE}=10V$
		Transition Frequency	f_T	250	MHz
Collector-Base Capacitance	C_{obo}		8	pF	$V_{CB}=10V, f=1MHz$
Delay Time	t_d		10	ns	$V_{CC}=30V, I_C=150mA$ $I_{B1}=I_{B2}=15mA$
Rise Time	t_r		10	ns	
Storage Time	t_s		225	ns	$V_{CC}=30V, I_C=150mA$
Fall Time	t_f		60	ns	$I_{B1}=I_{B2}=15mA$